

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

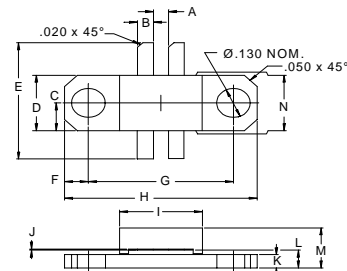
The **ASI CBSL30B** is Designed for Class AB, Cellular Base Station Applications up to 960 MHz.

**FEATURES:**

- Internal Input Matching Network
- $P_G = 7.5$  dB at 30 W/960 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	5.0 A
$V_{CBO}$	48 V
$V_{CES}$	45 V
$V_{EBO}$	4.0 V
$P_{DISS}$	43 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	3.0 °C/W

**PACKAGE STYLE .250 BAL FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.060 / 1.52	
B	.055 / 1.40	.065 / 1.65
C	.125 / 3.18	
D	.243 / 6.17	.255 / 6.48
E	.630 / 16.00	.670 / 17.01
F	.092 / 2.34	
G	.555 / 14.10	.565 / 14.35
H	.739 / 18.77	.750 / 19.05
I	.315 / 8.00	.327 / 8.31
J	.002 / 0.05	.006 / 0.15
K	.055 / 1.40	.065 / 1.65
L	.075 / 1.91	.095 / 2.41
M		.190 / 4.83
N	.245 / 6.22	.257 / 6.53

**ORDER CODE: ASI10583**
**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 50$ mA	48	50	---	V
$BV_{CEO}$	$I_C = 20$ mA	25	30	---	V
$BV_{EBO}$	$I_E = 5$ mA	3.5	4.0	---	V
$I_{CBO}$	$V_{CB} = 24$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 100$ mA	20		100	---
$C_{OB}$	$V_{CB} = 24$ V $f = 1.0$ MHz			25	pF
$P_G$	$V_{CC} = 24$ V $I_{CQ} = 2 \times 75$ mA $f = 960$ MHz $P_{OUT} = 30$ W	7.5			dB